

TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC3474

Switching Applications
Solenoid Drive Applications

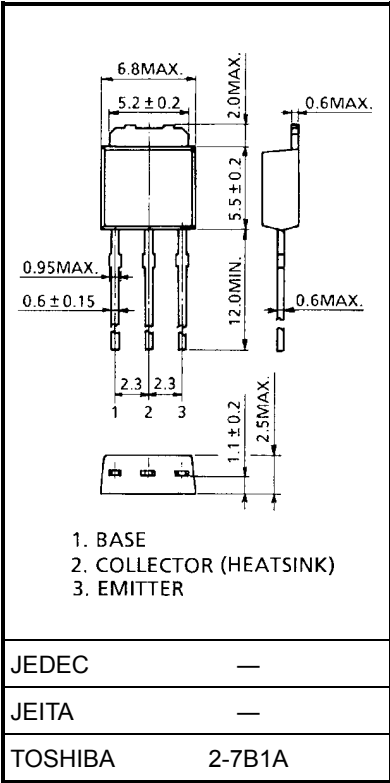
- High DC current gain: $h_{FE} = 500$ (min) ($I_C = 400$ mA)
- Low saturation voltage: $V_{CE(sat)} = 0.5$ V (max) ($I_C = 300$ mA)

Maximum Ratings (Ta = 25°C)

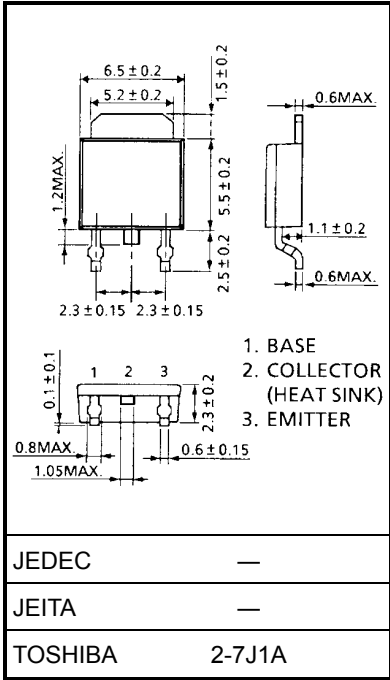
Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	80	V
Collector-emitter voltage		V_{CEO}	80	V
Emitter-base voltage		V_{EBO}	7	V
Collector current		I_C	2	A
Base current		I_B	0.5	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		20	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Industrial Applications

Unit: mm

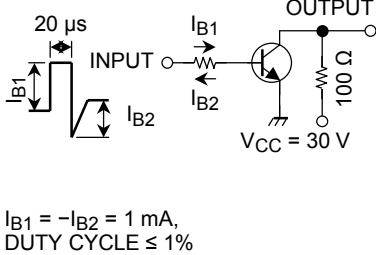


Weight: 0.36 g (typ.)

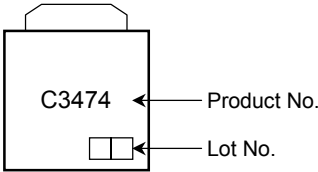


Weight: 0.36 g (typ.)

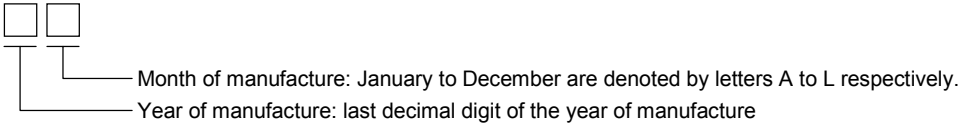
Electrical Characteristics (Ta = 25°C)

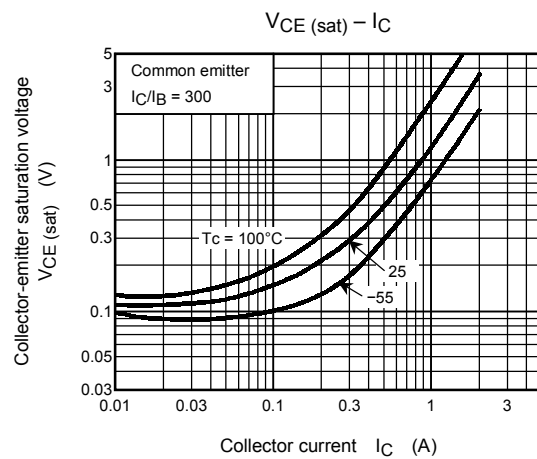
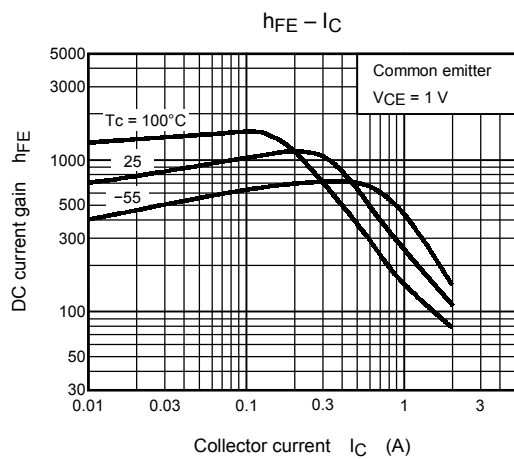
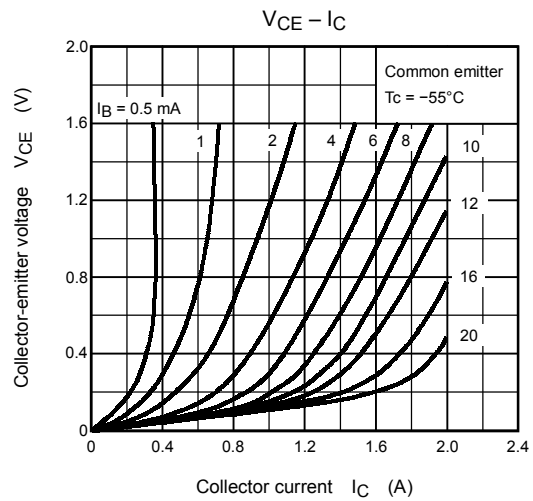
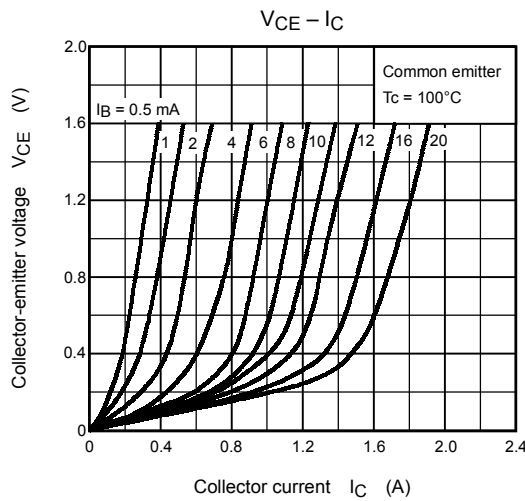
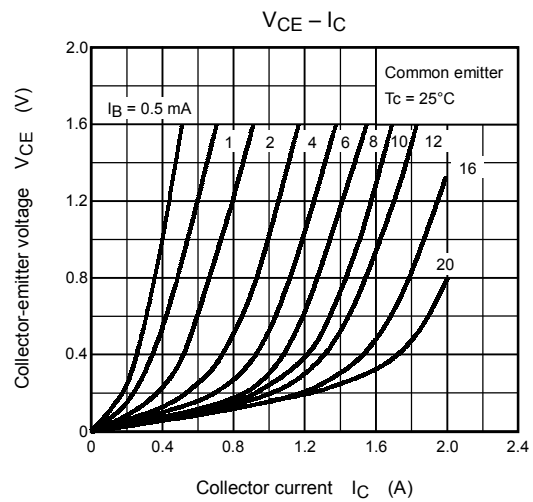
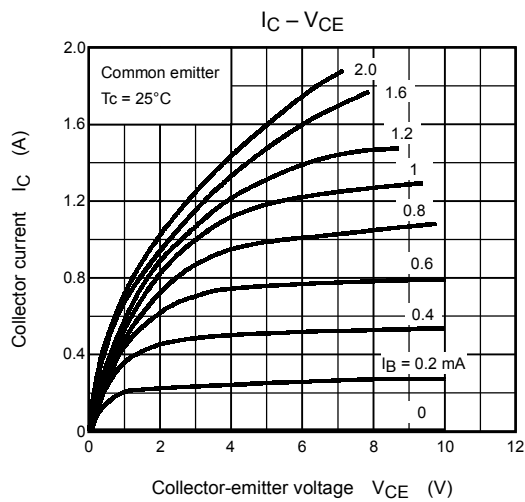
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		ICBO	V _{CB} = 80 V, I _E = 0	—	—	1	μA
Emitter cut-off current		IEBO	V _{EB} = 7 V, I _C = 0	—	—	1	μA
Collector-emitter breakdown voltage		V _(BR) CEO	I _C = 10 mA, I _B = 0	80	—	—	V
DC current gain		h _{FE}	V _{CE} = 1 V, I _C = 400 mA	500	—	—	
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 300 mA, I _B = 1 mA	—	0.3	0.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = 300 mA, I _B = 1 mA	—	—	1.1	V
Transition frequency		f _T	V _{CE} = 2 V, I _C = 100 mA	—	85	—	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	—	50	—	pF
Switching time	Turn-on time	t _{on}		—	2	—	μs
	Storage time	t _{stg}		—	5	—	
	Fall time	t _f		—	2	—	

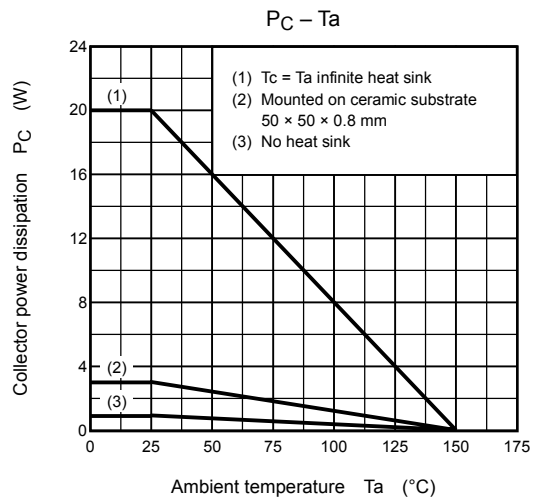
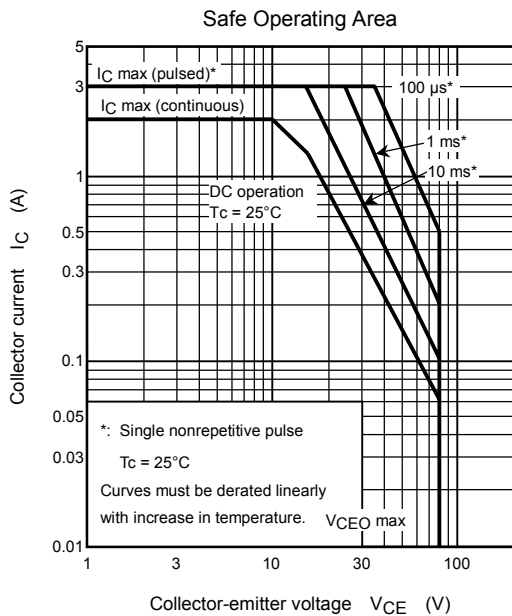
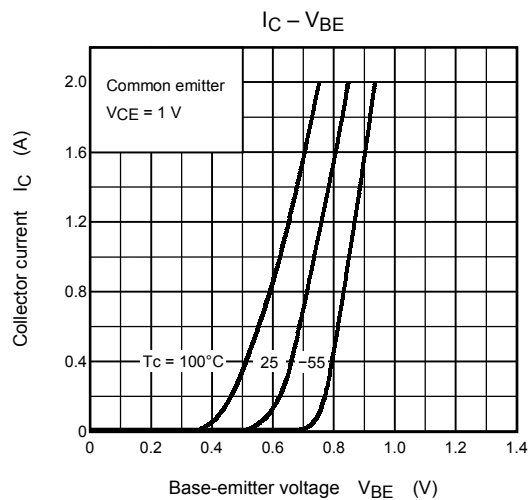
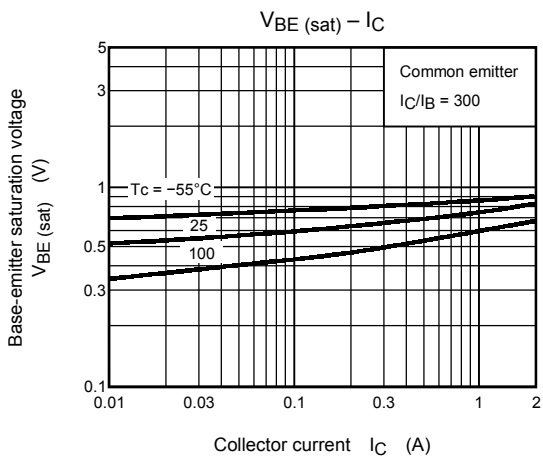
Marking



Explanation of Lot No.







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